











THVD1410 THVD1450, THVD1451, THVD1452

SLLSEY3E -MAY 2018-REVISED MAY 2019

THVD14xx 3.3-V to 5-V RS-485 Transceivers with ±18-kV IEC ESD Protection

Features

- Meets or Exceeds the Requirements of the TIA/EIA-485A Standard
- 3 V to 5.5 V Supply Voltage
- Differential Output Exceeds 2.1 V for PROFIBUS Compatibility with 5-V Supply
- Bus I/O ESD Protection
 - ±30 kV HBM
 - ±18 kV IEC 61000-4-2 Contact Discharge
 - ±25 kV IEC 61000-4-2 Air-Gap Discharge
 - ±4 kV IEC 61000-4-4 Fast Transient Burst
- **Extended Operational Common-mode** Range: ±15 V
- Low EMI 500 kbps and 50 Mbps Data Rates
- Large Receiver Hysteresis for Noise Rejection
- Low Power Consumption
 - Standby Supply Current: < 1 μA
 - Current During Operation: < 3 mA
- **Extended Ambient Temperature** Range: -40°C to 125°C
- Glitch-Free Power-Up/Down for Hot Plug-in Capability
- Open, Short, and Idle Bus Failsafe
- 1/8 Unit Load (Up to 256 Bus Nodes)
- Small-Size VSON and VSSOP Packages Save Board Space or SOIC for Drop-in Compatibility

Applications

- Motor Drives
- Factory Automation & Control
- **Grid Infrastructure**
- **Building Automation**
- **HVAC Systems**
- Video Surveillance
- **Process Analytics**
- Wireless Infrastructure

3 Description

THVD14xx is a family of noise-immune RS-485/RS-422 transceivers designed to operate in rugged industrial environments. The bus pins of these devices are robust to high levels of IEC electrical fast transients (EFT) and IEC electrostatic discharge (ESD) events, eliminating the need for additional system level protection components.

Each of these devices operates from a single supply between 3 V and 5.5 V. The devices in this family feature an extended common-mode voltage range them suitable for multi-point makes applications over long cable runs.

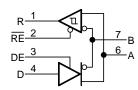
THVD14xx family of devices is available in small VSON and VSSOP packages for space constrained applications. These devices are characterized over ambient free-air temperatures from -40°C to 125°C.

Device Information⁽¹⁾

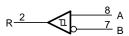
PART NUMBER	PACKAGE	BODY SIZE (NOM)
THVD1410	VSSOP (8)	3.00 mm × 3.00 mm
1001410	SOIC (8)	4.90 mm × 3.91 mm
	VSON (8)	3.00 mm × 3.00 mm
THVD1450	VSSOP (8)	3.00 mm × 3.00 mm
	SOIC (8)	4.90 mm x 3.91 mm
THVD1451	VSON (8)	3.00 mm × 3.00 mm
1001451	SOIC (8)	4.90 mm x 3.91 mm
THVD1452	VSSOP (10)	3.00 mm × 3.00 mm
101402	SOIC (14)	8.65 mm × 3.91 mm

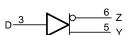
(1) For all available packages, see the orderable addendum at the end of the data sheet.

THVD1410 and THVD1450 Simplified Schematic

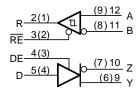


THVD1451 Simplified Schematic





THVD1452 Simplified Schematic



Features 1

Applications 1



Table of Contents

3	Description	1		9.3 Feature Description	
4	4 Revision History	<u>2</u>		9.4 Device Functional Modes	
5	5 Device Comparison Table	4	10	Application and Implementation	
6	Pin Configuration and Functions	5		10.1 Application Information	
7	7 Specifications	8	4.4	10.2 Typical Application	
	7.1 Absolute Maximum Ratings		11	Power Supply Recommendations	
	7.2 ESD Ratings	8	12	Layout	
	7.3 ESD Ratings [IEC]	8		12.1 Layout Guidelines	
	7.4 Recommended Operating Conditions		40	12.2 Layout Example	
	7.5 Thermal Information	9	13	Device and Documentation Support	
	7.6 Power Dissipation			13.1 Device Support	
	7.7 Electrical Characteristics			13.2 Third-Party Products Disclaimer	
	7.8 Switching Characteristics			13.3 Related Links13.4 Receiving Notification of Documentation	
	7.9 Typical Characteristics: All Devices			13.5 Community Resources	
	7.10 Typical Characteristics: THD1450, THVD1451 THVD1452			13.6 Trademarks	
	7.11 Typical Characteristics: THVD1410			13.7 Electrostatic Discharge Caution	
8				13.8 Glossary	
9			14	Mechanical, Packaging, and Orderable	
-	betailed Description	10		Information	
	Changed THVD1451 From: Product Preview To: F				
	anges from Revision C (February 2019) to Revis Changed THVD1410 From: Product Preview To: F		4-1-		Page
			uala		
	anges from Revision B (December 2018) to Revi				Page
<u> </u>	Changed THVD1452 From: Product Preview To: F	Production	data		1
Cha	anges from Revision A (May 2018) to Revision E	В			Page
•	Added Feature: "Differential Output Exceeds 2.1 V	/"			1
	Changed Feature: ±18 kV IEC 61000-4-2 Air-Gap				
•	Added SOIC (8) package to THVD1451				1
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INSTRUMENTS

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•	Added condition to Figure 8 to Figure 3	14
•	Added Typical Characteristics, THD1410	
•	Changed A to A/Y and B to B/Z in Figure 20 to Figure 24	
•	Added 3rd paragraph to the Overview section	
Cha	anges from Original (November 2017) to Revision A	Page
•	Changed the document status From: Advanced Information To: Production Mix dat	ta 1



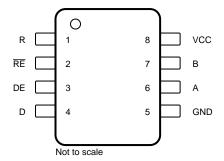
5 Device Comparison Table

PART NUMBER	DUPLEX	ENABLES	SIGNALING RATE	NODES
THVD1410	Half	DE, RE	up to 500 kbps	
THVD1450	Half	DE, RE		050
THVD1451	Full	None	up to 50 Mbps	256
THVD1452	Full	DE, RE		

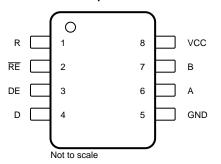


6 Pin Configuration and Functions

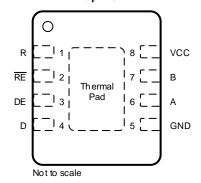
THVD1410, THVD1450 Devices 8-Pin D Package (SOIC) Top View



THVD1410, THVD1450 Devices 8-Pin DGK Package (VSSOP) Top View



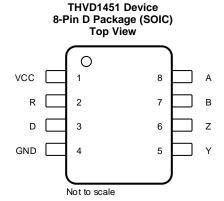
THVD1450 Device 8-Pin DRB Package (VSON) Top View



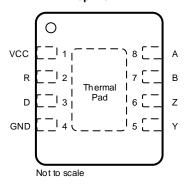
Pin Functions

	P	IN		1/0	DESCRIPTION		
NAME	D	DGK	DRB	I/O	DESCRIPTION		
Α	6	6	6	Bus input/output	Bus I/O port, A (complementary to B)		
В	7	7	7	Bus input/output	Bus I/O port, B (complementary to A)		
D	4	4	4	Digital input	Driver data input		
DE	3	3	3	Digital input Driver enable, active high (2-MΩ internal pull-down)			
GND	5	5	5	Ground Device ground			
R	1	1	1	Digital output	Receive data output		
V_{CC}	8	8	8	Power	3.3-V to 5-V supply		
RE	2	2	2	Digital input	Digital input Receiver enable, active low (2-MΩ internal pull-up)		
Thermal Pad	_	_		I/O	No electrical connection. Should be connected to GND for optimal thermal performance.		





THVD1451 Device 8-Pin DRB Package (VSON) Top View



Pin Functions

	PIN		1/0	Recognition		
NAME			1/0	Description		
Α	8	8	Bus input	Bus input, A (complementary to B)		
В	7	7	Bus input	Bus input, B (complementary to A)		
D	3	3	Digital input	Driver data input		
GND	4	4	Ground	Ground Device ground		
R	2	2	Digital output Receive data output			
V _{CC}	1	1	Power	3.3-V to 5-V supply		
Υ	5	5	Bus output	Digital bus output, Y (Complementary to Z)		
Z	6	6	Bus output	Digital bus output, Z (Complementary to Y)		
Thermal Pad	_		I/O	No electrical connection. Should be connected to GND for optimal thermal performance.		



14-Pin D Package (SOIC) Top View NC VCC 14 R 2 13 VCC RE 3 12 DE 11 В D 5 10 Ζ GND 6 9 Υ GND 8 NC Not to scale

THVD1452 Device

10-Pin DGS Package (VSSOP) **Top View** 0 VCC R 10 $\overline{\mathsf{RE}}$ 2 9 Α 3 8 В DE D 7 Ζ Υ GND 5 6 Not to scale

THVD1452 Device

NC - No internal connection

Pin Functions

	P	IN	1/0	DESCRIPTION		
NAME	NAME D DGS		1/0	DESCRIPTION		
Α	12	9	Bus input	Bus input, A (complementary to B)		
В	11	8	Bus input	Bus input, B (complementary to A)		
D	5	4	Digital input	Driver data input		
DE	4	3	Digital input Driver enable, active high (2-MΩ internal pull-down)			
GND	6, 7 ⁽¹⁾	5	Ground Device ground			
NC	1, 8	_	_	Internally not connected		
R	2	1	Digital output	Receive data output		
V_{CC}	13, 14 ⁽¹⁾	10	Power	3.3-V to 5-V supply		
Υ	9	6	Bus output	Digital bus output, Y (Complementary to Z)		
Z	10	7	Bus output	Digital bus output, Z (Complementary to Y)		
RE	3	2	Digital input	Receiver enable, active low (2-M Ω internal pull-up)		

⁽¹⁾ These pins are internally connected



7 Specifications

7.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted) (1)

		MIN	MAX	UNIT
Supply voltage	V _{CC}	-0.5	7	V
Bus voltage	Range at any bus pin (A, B, Y, or Z) as differential or common-mode with respect to GND	-18	18	V
Input voltage	Range at any logic pin (D, DE, or RE)	-0.3	5.7	V
Receiver output current	Io	-24	24	mA
Storage temperate	ure range	-65	150	°C

⁽¹⁾ Stresses beyond those listed under Absolute Maximum Ratings may cause permanent damage to the device. These are stress ratings only, which do not imply functional operation of the device at these or any other conditions beyond those indicated under Recommended Operating Conditions. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

7.2 ESD Ratings

				VALUE	UNIT
		Human body model (HBM), per ANSI/ESDA/JEDEC JS-001 (1)	Bus pins and GND	±30	kV
		ANSI/ESDA/JEDEC JS-001	All other pins	±8	kV
V _(ESD)	Electrostatic discharge	Charged device model (CDM), per JEDEC JESD22-C101 ⁽²⁾	All pins	±1.5	kV
		Machine model (MM), per JEDEC JESD22-A115-A	All pins	±200	V

⁽¹⁾ JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.

7.3 ESD Ratings [IEC]

	-			VALUE	UNIT
.,	Electrostatic disabores	Contact discharge, per IEC 61000-4-2	Bus pins and GND	±18	kV
V _(ESD)	Electrostatic discharge	Air-gap discharge, per IEC 61000-4-2	Bus pins and GND	±25	kV
V _(EFT)	Electrical fast transient	Per IEC 61000-4-4	Bus pins and GND	±4	kV

²⁾ JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.



7.4 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)

		MIN	NOM	MAX	UNIT
V _{CC}	Supply voltage	3		5.5	V
VI	Input voltage at any bus terminal ⁽¹⁾	-15		15	V
V _{IH}	High-level input voltage (driver, driver enable, and receiver enable inputs)	2		V _{CC}	V
V _{IL}	Low-level input voltage (driver, driver enable, and receiver enable inputs)	0		0.8	V
V _{ID}	Differential input voltage	-15		15	V
lo	Output current, driver	-60		60	mA
I _{OR}	Output current, receiver	-8		8	mA
R_L	Differential load resistance	54			Ω
1/t _{UI}	Signaling rate: THVD1410			500	kbps
1/t _{UI}	Signaling rate: THVD1450, THVD1451, THVD1452			50	Mbps
T _A	Operating ambient temperature	-40		125	°C
TJ	Junction temperature	-40		150	°C

⁽¹⁾ The algebraic convention, in which the least positive (most negative) limit is designated as minimum is used in this data sheet.

7.5 Thermal Information

1.5							
	THERMAL METRIC ⁽¹⁾	THVD1410 THVD1450 THVD1451	THVD1452	THVD1410 THVD1450	THVD1452	THVD1450 THVD1451	UNIT
		D (SOIC)	D (SOIC)	DGK (VSSOP)	DGS (VSSOP)	DRB (VSON)	
		8 PINS	14 PINS	8 PINS	10 PINS	8 PINS	
$R_{\theta JA}$	Junction-to-ambient thermal resistance	114.3	86.4	155.2	155.6	48.6	°C/W
R _{θJC(to}	Junction-to-case (top) thermal resistance	56.7	43.7	47.2	49.3	49.1	°C/W
$R_{\theta JB}$	Junction-to-board thermal resistance	57.7	42.5	76.1	77.1	21.1	°C/W
Ψ_{JT}	Junction-to-top characterization parameter	12.8	10.2	3.9	4.5	0.8	°C/W
Ψ_{JB}	Junction-to-board characterization parameter	57	42.2	74.8	75.7	21.1	°C/W
$\begin{array}{c} R_{\theta JC(b} \\ \text{ot)} \end{array}$	Junction-to-case (bottom) thermal resistance	N/A	N/A	N/A	N/A	2.7	°C/W

⁽¹⁾ For more information about traditional and new thermal metrics, see the Semiconductor and IC Package Thermal Metrics application report.

7.6 Power Dissipation

PARAMETE R	Description	TEST CONDITIONS	MIN	TYP	MAX	UNIT
	Driver and receiver enabled, $V_{CC} = 5.5$	Unterminated: $R_L = 300 \Omega$, $C_L = 50 pF$	360			mW
	V , $T_A = 125^{0}$ C, 50% duty cycle square wave at 500kbps signaling rate,	RS-422 load: $R_L = 100 \Omega$, $C_L = 50 pF$		370		mW
В	THVD1410	RS-485 load: $R_L = 54 \Omega$, $C_L = 50 pF$		410		mW
P _D	Driver and receiver enabled, $V_{CC} = 5.5$	Unterminated: $R_L = 300 \Omega$, $C_L = 50 pF$		360		mW
	V, T _A = 125 ⁰ C, 50% duty cycle square wave at 50Mbps signaling rate,	RS-422 load: $R_L = 100 \Omega$, $C_L = 50 pF$		320		mW
	THVD145x devices	RS-485 load: $R_L = 54 \Omega$, $C_L = 50 pF$		330		mW



7.7 Electrical Characteristics

over operating free-air temperature range (unless otherwise noted). All typical values are at 25°C and supply voltage of V_{CC} = 5 V.

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT	
Driver							
		$R_L = 60 \Omega$, -15 V \leq V _{test} \leq 15 V (Se Figure 20) ⁽¹⁾	ее	1.5	3.5		V
V _{OD}	Driver differential output voltage magnitude	R_L = 60 Ω, -15 V ≤ V _{test} ≤ 15 V, 4.5 5.5 V, (See Figure 20)	5 V ≤ V _{CC} ≤	2.1			V
		$R_L = 100 \Omega$ (See Figure 21)		2	4		V
		$R_L = 54 \Omega$ (See Figure 21)		1.5	3.5		V
$\Delta V_{OD} $	Change in differential output voltage			-200		200	mV
V _{oc}	Common-mode output voltage	$R_L = 54 \Omega$ (See Figure 21)		1	V _{CC} /2	3	V
$\Delta V_{OC(SS)}$	Change in steady-state common- mode output voltage			-200		200	mV
Ios	Short-circuit output current	$DE = V_{CC}$, -7 $V \le V_O \le 12 V$		-250		250	mA
Receiver							
		DE - 0.V. V 0.V. or 5.5.V.	V _I = 12V		50	125	μΑ
	Pug input ourrent	$DE = 0 \text{ V}, \text{ V}_{CC} = 0 \text{ V or } 5.5 \text{ V}$	$V_I = -7V$	-100	-65		μΑ
l _l	Bus input current	DE - 0.V. V 0.V. or 5.5.V.	V _I = 15V		60	125	μΑ
		$DE = 0 \text{ V}, \text{ V}_{CC} = 0 \text{ V or } 5.5 \text{ V}$	-200	-130		μΑ	
V _{TH+}	Positive-going input threshold voltage		See ⁽²⁾	-100	-20	mV	
V _{TH} -	Negative-going input threshold voltage	Over common-mode range of ± 15	5 V	-200	-130	See ⁽²⁾	mV
V _{HYS}	Input hysteresis				30		mV
V_{OH}	Output high voltage	I _{OH} = -8 mA		V _{CC} – 0.4	V _{CC} – 0.2		V
V _{OL}	Output low voltage	I _{OL} = 8 mA			0.2	0.4	V
I _{OZR}	Output high-impedance current	$V_O = 0 \text{ V or } V_{CC}, \overline{RE} = V_{CC}$		-1		1	μΑ
Logic	•	•		*		·	
I _{IN}	Input current (D, DE, RE)	$3 \text{ V} \le \text{V}_{CC} \le 5.5 \text{ V}, 0 \text{ V} \le \text{V}_{IN} \le \text{V}_{CC}$)	-6.2		6.2	μA
Device							
		Driver and receiver enabled	$\overline{RE} = 0 \text{ V}$, $DE = V_{CC}$, No load		2.4	3	mA
		Driver enabled, receiver disabled	$\overline{RE} = V_{CC},$ $DE = V_{CC},$ No load		2	2.5	mA
Supply current (quiescent)		Driver disabled, receiver enabled	RE = 0 V, DE = 0 V, No load		700	960	μΑ
		Driver and receiver disabled RE = V _{CC} DE = 0 V = open, N load			0.1	1	μΑ

 $[|]V_{OD}| \ge 1.4$ V when $T_A > 85$ °C, $V_{test} < -7$ V and $V_{CC} < 3.135$ V. Under any specific conditions, V_{TH+} is assured to be at least V_{HYS} higher than V_{TH-} .

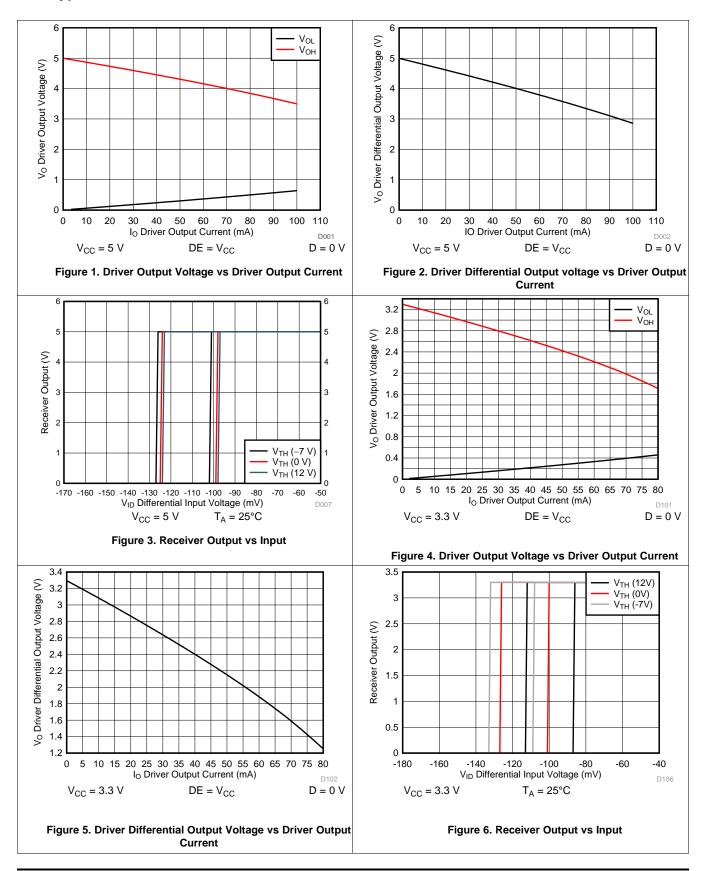


7.8 Switching Characteristics

over operating free-air temperature range (unless otherwise noted). All typical values are at 25°C and supply voltage of $V_{CC} = 5 \text{ V}$

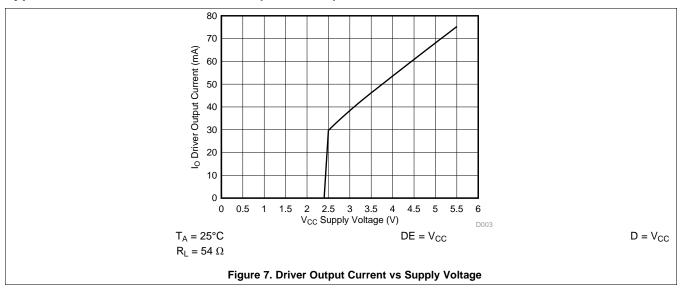
	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Driver: THVD	1410					
t _r , t _f	Differential output rise/fall time		250	460	680	ns
t _{PHL} , t _{PLH}	Propagation delay	$R_L = 54 \Omega$, $C_L = 50 pF$, See Figure 22		250	500	ns
t _{SK(P)}	Pulse skew, t _{PHL} - t _{PLH}				10	ns
t _{PHZ} , t _{PLZ}	Disable time			80	200	ns
t t	Enable time	RE = 0 V, See Figure 23 and Figure 24		100	600	ns
t _{PZH} , t _{PZL}	Enable time	RE = V _{CC} , See Figure 23 and Figure 24		4	11	μs
Receiver: TH	VD1410					
t _r , t _f	Output rise/fall time			10	20	ns
t _{PHL} , t _{PLH}	Propagation delay	C _L = 15 pF, See Figure 25		35	110	ns
t _{SK(P)}	Pulse skew, t _{PHL} - t _{PLH}				7	ns
t _{PHZ} , t _{PLZ}	Disable time			30	60	ns
t _{PZH(1)} , t _{PZL(1)} ,		DE = V _{CC} , See Figure 26		60	140	ns
$t_{PZH(2)},$ $t_{PZL(2)},$	Enable time	DE = 0 V, See Figure 27		6	14	μs
Driver: THVD	1450, THVD1451, THVD1452					
t _r , t _f	Differential output rise/fall time		1	3	6	ns
t _{PHL} , t _{PLH}	Propagation delay	$R_L = 54 \Omega$, $C_L = 50 pF$, See Figure 22	3	10	20	ns
t _{SK(P)}	Pulse skew, t _{PHL} - t _{PLH}				3.5	ns
t_{PHZ} , t_{PLZ}	Disable time			15	25	ns
	Enable time	RE = 0 V, See Figure 23 and Figure 24		20	50	ns
t _{PZH} , t _{PZL}	Enable time	RE = V _{CC} , See Figure 23 and Figure 24		2.5	10	μs
Receiver: TH	VD1450, THVD1451, THVD1452				*	
t _r , t _f	Output rise/fall time			2	6	ns
t _{PHL} , t _{PLH}	Propagation delay	C _L = 15 pF, See Figure 25		25	40	ns
t _{SK(P)}	Pulse skew, t _{PHL} - t _{PLH}				3.5	ns
t _{PHZ} , t _{PLZ}	Disable time			14	28	ns
t _{PZH(1)} , t _{PZL(1)} ,		DE = V _{CC} , See Figure 26		50	110	ns
$t_{PZH(2)},$ $t_{PZL(2)},$	Enable time	DE = 0V, See Figure 27		4	14	μs

7.9 Typical Characteristics: All Devices



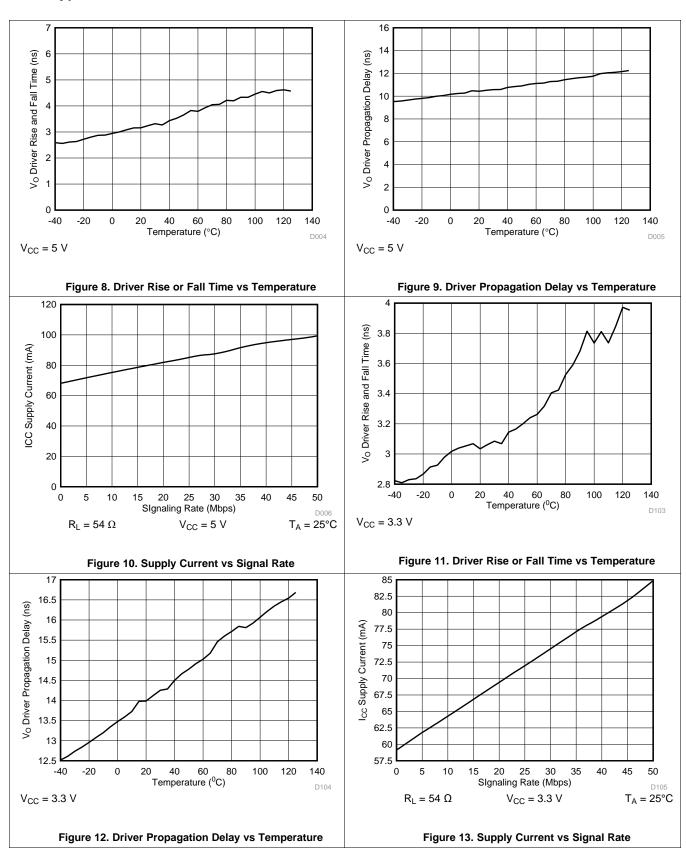


Typical Characteristics: All Devices (continued)



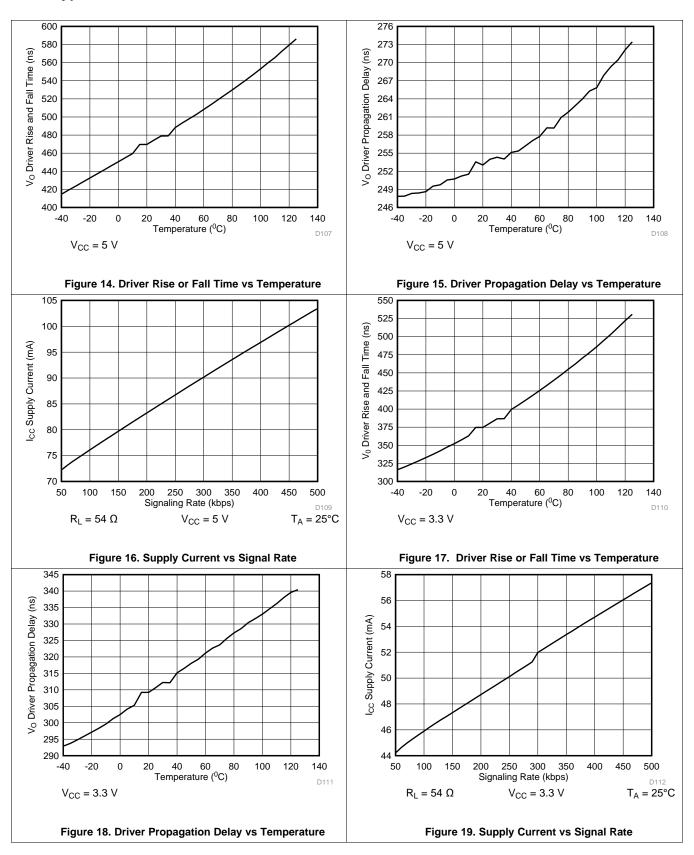


7.10 Typical Characteristics: THD1450, THVD1451 and THVD1452





7.11 Typical Characteristics: THVD1410



8 Parameter Measurement Information

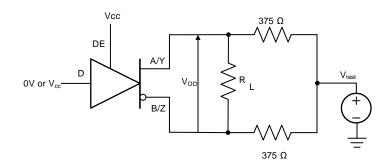


Figure 20. Measurement of Driver Differential Output Voltage With Common-Mode Load

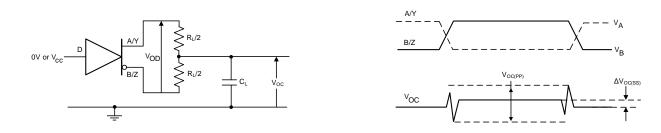


Figure 21. Measurement of Driver Differential and Common-Mode Output With RS-485 Load

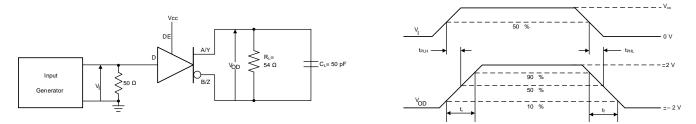


Figure 22. Measurement of Driver Differential Output Rise and Fall Times and Propagation Delays

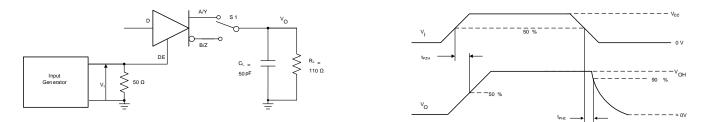


Figure 23. Measurement of Driver Enable and Disable Times With Active High Output and Pull-Down Load



Parameter Measurement Information (continued)

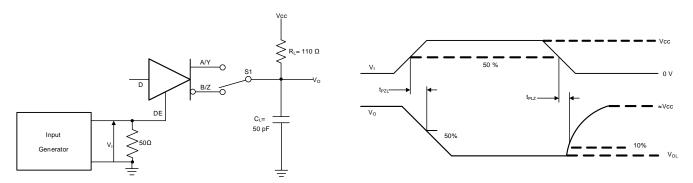


Figure 24. Measurement of Driver Enable and Disable Times With Active Low Output and Pull-up Load

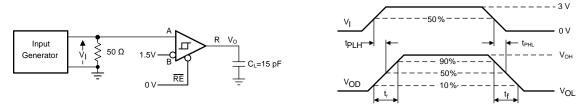


Figure 25. Measurement of Receiver Output Rise and Fall Times and Propagation Delays

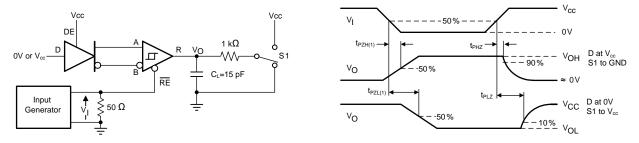


Figure 26. Measurement of Receiver Enable/Disable Times With Driver Enabled

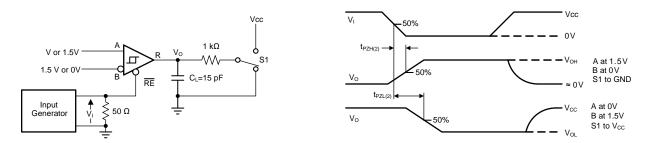


Figure 27. Measurement of Receiver Enable Times With Driver Disabled

9 Detailed Description

9.1 Overview

THVD1410 and THVD1450 are low-power, half duplex RS-485 transceivers available in two speed grades suitable for data transmission up to 500 kbps and 50 Mbps respectively.

THVD1451 is fully enabled with no external enabling pins. THVD1452 has active-high driver enable and active-low receiver enable. A standby current of less than 1 µA can be achieved by disabling both driver and receiver.

THVD14xx family of devices have a higher typical differential output voltage (V_{OD}) than traditional transceivers for better noise immunity. A minimum differential output voltage of 2.1 V is specified with V_{CC} voltage of 5 V ±10% to meet the requirements of PROFIBUS applications.

9.2 Functional Block Diagrams

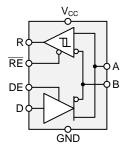


Figure 28. THVD1410 and THVD1450

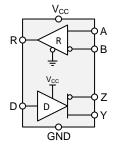


Figure 29. THVD1451

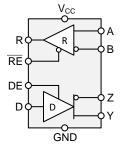


Figure 30. THVD1452



9.3 Feature Description

Internal ESD protection circuits protect the transceiver against electrostatic discharges (ESD) according to IEC 61000-4-2 of up to ±18 kV and against electrical fast transients (EFT) according to IEC 61000-4-4 of up to ±4 kV. With careful system design, one could achieve ±4 kV EFT Criterion A (no data loss when transient noise is present).

The THVD14xx device family provides internal biasing of the receiver input thresholds in combination with large input-threshold hysteresis. The receiver output remains logic high under a bus-idle or bus-short conditions without the need for external failsafe biasing resistors. Device operation is specified over a wide ambient temperature range from -40°C to 125°C.

9.4 Device Functional Modes

9.4.1 Device Functional Modes for THVD1410 and THVD1450

When the driver enable pin, DE, is logic high, the differential outputs A and B follow the logic states at data input D. A logic high at D causes A to turn high and B to turn low. In this case the differential output voltage defined as $V_{OD} = V_A - V_B$ is positive. When D is low, the output states reverse: B turns high, A becomes low, and V_{OD} is negative.

When DE is low, both outputs turn high-impedance. In this condition the logic state at D is irrelevant. The DE pin has an internal pull-down resistor to ground, thus when left open the driver is disabled (high-impedance) by default. The D pin has an internal pull-up resistor to V_{CC} , thus, when left open while the driver is enabled, output A turns high and B turns low.

		o a	unio =	-
FUNCTION	PUTS	OUTI	ENABLE	INPUT
FUNCTION	В	Α	DE	D
Actively drive bus high	L	Н	Н	Н
Actively drive bus low	Н	L	Н	L
Driver disabled	Z	Z	L	Χ
Driver disabled by default	Z	Z	OPEN	Х
Actively drive bus high by default	L	Н	Н	OPEN

Table 1. Driver Function Table for THVD1410 and THVD1450

When the receiver enable pin, \overline{RE} , is logic low, the receiver is enabled. When the differential input voltage defined as $V_{ID} = V_A - V_B$ is higher than the positive input threshold, V_{TH+} , the receiver output, R, turns high. When V_{ID} is lower than the negative input threshold, V_{TH-} , the receiver output, R, turns low. If V_{ID} is between V_{TH+} and V_{TH-} the output is indeterminate.

When $\overline{\text{RE}}$ is logic high or left open, the receiver output is high-impedance and the magnitude and polarity of V_{ID} are irrelevant. Internal biasing of the receiver inputs causes the output to go failsafe-high when the transceiver is disconnected from the bus (open-circuit), the bus lines are shorted to one another (short-circuit), or the bus is not actively driven (idle bus).

Table 2. Receiver Function Table for THVD1410 and THVD1450

DIFFERENTIAL INPUT	ENABLE	OUTPUT	FUNCTION
$V_{ID} = V_A - V_B$	RE	R	FUNCTION
$V_{TH+} < V_{ID}$	L	Н	Receive valid bus high
$V_{TH-} < V_{ID} < V_{TH+}$	L	?	Indeterminate bus state
$V_{ID} < V_{TH}$	L	L	Receive valid bus low
X	Н	Z	Receiver disabled
X	OPEN	Z	Receiver disabled by default
Open-circuit bus	L	Н	Fail-safe high output
Short-circuit bus	L	Н	Fail-safe high output
Idle (terminated) bus	L	Н	Fail-safe high output

9.4.2 Device Functional Modes for THVD1451

For this device, the driver and receiver are fully enabled, thus the differential outputs Y and Z follow the logic states at data input D at all times. A logic high at D causes Y to turn high and Z to turn low. In this case, the differential output voltage defined as $V_{OD} = V_Y - V_Z$ is positive. When D is low, the output states reverse: Z turns high, Y becomes low, and VOD is negative. The D pin has an internal pull-up resistor to V_{CC} , thus, when left open while the driver is enabled, output Y turns high and Z turns low.

Table 3. Driver Function Table for THVD1451

INPUT	OUTI	PUTS	FUNCTIONS	
D	Y	Z	FUNCTIONS	
Н	Н	L	Actively drive bus high	
L	L	Н	Actively drive bus low	
OPEN	Н	L	Actively drive bus High by default	

When the differential input voltage defined as $V_{ID} = V_A - V_B$ is higher than the positive input threshold, V_{TH+} , the receiver output, R, turns high. When V_{ID} is less than the negative input threshold, V_{TH-} , the receiver output, R, turns low. If V_{ID} is between V_{TH+} and V_{TH-} the output is indeterminate. Internal biasing of the receiver inputs causes the output to go failsafe-high when the transceiver is disconnected from the bus (open-circuit), the bus lines are shorted to one another (short-circuit), or the bus is not actively driven (idle bus).

Table 4. Receiver Function Table for THVD1451

DIFFERENTIAL INPUT	OUTPUT	FUNCTION
$V_{ID} = V_A - V_B$	R	FUNCTION
$V_{TH+} < V_{ID}$	Н	Receive valid bus high
$V_{TH-} < V_{ID} < V_{TH+}$?	Indeterminate bus state
$V_{ID} < V_{TH-}$	L	Receive valid bus low
Open-circuit bus	Н	Fail-safe high output
Short-circuit bus	Н	Fail-safe high output
Idle (terminated) bus	Н	Fail-safe high output



9.4.3 Device Functional Modes for THVD1452

When the driver enable pin, DE, is logic high, the differential outputs Y and Z follow the logic states at data input D. A logic high at D causes Y to turn high and Z to turn low. In this case the differential output voltage defined as $V_{OD} = V_Y - V_Z$ is positive. When D is low, the output states reverse: Z turns high, Y becomes low, and V_{OD} is negative.

When DE is low, both outputs turn high-impedance. In this condition the logic state at D is irrelevant. The DE pin has an internal pull-down resistor to ground, thus when left open the driver is disabled (high-impedance) by default. The D pin has an internal pull-up resistor to V_{CC} , thus, when left open while the driver is enabled, output Y turns high and Z turns low.

OUTPUTS INPUT ENABLE FUNCTION DE Υ Z D Н Н Н L Actively drive bus high L Н L Н Actively drive bus low Z Χ L Ζ Driver disabled Χ **OPEN** Ζ Ζ Driver disabled by default **OPEN** Н Actively drive bus high by default

Table 5. Driver Function Table for THVD1452

When the receiver enable pin, \overline{RE} , is logic low, the receiver is enabled. When the differential input voltage defined as $V_{ID} = V_A - V_B$ is higher than the positive input threshold, V_{TH+} , the receiver output, R, turns low. If V_{ID} is between V_{TH+} and V_{TH-} the output is indeterminate.

When \overline{RE} is logic high or left open, the receiver output is high-impedance and the magnitude and polarity of V_{ID} are irrelevant. Internal biasing of the receiver inputs causes the output to go failsafe-high when the transceiver is disconnected from the bus (open-circuit), the bus lines are shorted to one another (short-circuit), or the bus is not actively driven (idle bus).

DIFFERENTIAL INPUT ENABLE OUTPUT FUNCTION $V_{ID} = V_A - V_B$ RE R $V_{TH+} < V_{ID}$ L Н Receive valid bus high $V_{TH\text{-}} < V_{ID} < V_{TH\text{+}}$ L ? Indeterminate bus state $V_{\text{ID}} < V_{\text{TH}}$ L L Receive valid bus low Н Z Receiver disabled Χ Χ **OPEN** Ζ Receiver disabled by default Open-circuit bus Н 1 Fail-safe high output L Н Short-circuit bus Fail-safe high output Н L Fail-safe high output Idle (terminated) bus

Table 6. Receiver Function Table for THVD1452

10 Application and Implementation

NOTE

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

10.1 Application Information

The THVD14xx family consists of half-duplex and full-duplex RS-485 transceivers commonly used for asynchronous data transmissions. For half-duplex devices, the driver and receiver enable pins allow for the configuration of different operating modes. Full-duplex implementation requires two signal pairs (four wires), and allows each node to transmit data on one pair while simultaneously receiving data on the other pair.

10.2 Typical Application

An RS-485 bus consists of multiple transceivers connecting in parallel to a bus cable. To eliminate line reflections, each cable end is terminated with a termination resistor, R_T , whose value matches the characteristic impedance, Z_0 , of the cable. This method, known as parallel termination, generally allows for higher data rates over longer cable length.

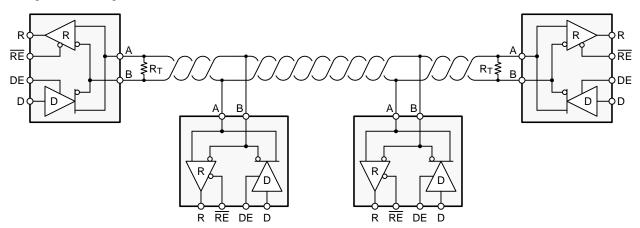


Figure 31. Typical RS-485 Network With Half-Duplex Transceivers

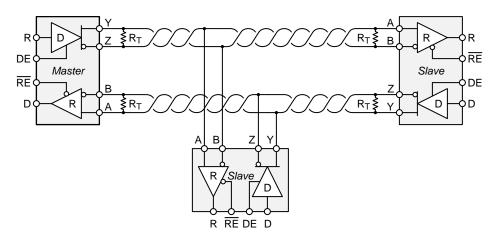


Figure 32. Typical RS-485 Network With Full-Duplex Transceivers



10.2.1 Design Requirements

RS-485 is a robust electrical standard suitable for long-distance networking that may be used in a wide range of applications with varying requirements, such as distance, data rate, and number of nodes.

10.2.1.1 Data Rate and Bus Length

There is an inverse relationship between data rate and cable length, which means the higher the data rate, the short the cable length; and conversely, the lower the data rate, the longer the cable length. While most RS-485 systems use data rates between 10 kbps and 100 kbps, some applications require data rates up to 250 kbps at distances of 4000 feet and longer. Longer distances are possible by allowing for small signal jitter of up to 5 or 10%.

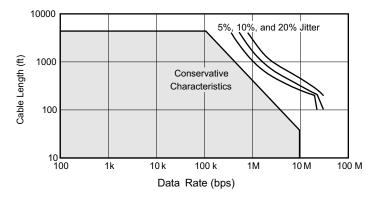


Figure 33. Cable Length vs Data Rate Characteristic

Even higher data rates are achievable (that is, 50 Mbps for the THVD1450, THVD1451 and THVD1452) in cases where the interconnect is short enough (or has suitably low attenuation at signal frequencies) to not degrade the data.

10.2.1.2 Stub Length

When connecting a node to the bus, the distance between the transceiver inputs and the cable trunk, known as the stub, should be as short as possible. Stubs present a non-terminated piece of bus line which can introduce reflections of varying phase as the length of the stub increases. As a general guideline, the electrical length, or round-trip delay, of a stub should be less than one-tenth of the rise time of the driver, thus giving a maximum physical stub length as shown in Equation 1.

 $L_{(STUB)} \le 0.1 \times t_r \times v \times c$

where

- t_r is the 10/90 rise time of the driver
- c is the speed of light $(3 \times 10^8 \text{ m/s})$
- v is the signal velocity of the cable or trace as a factor of c

10.2.1.3 Bus Loading

The RS-485 standard specifies that a compliant driver must be able to drive 32 unit loads (UL), where 1 unit load represents a load impedance of approximately 12 k Ω . Because the THVD14xx family consists of 1/8 UL transceivers, connecting up to 256 receivers to the bus is possible.

(1)



10.2.1.4 Receiver Failsafe

The differential receivers of the THVD14xx family are failsafe to invalid bus states caused by the following:

- · Open bus conditions, such as a disconnected connector
- Shorted bus conditions, such as cable damage shorting the twisted-pair together
- · Idle bus conditions that occur when no driver on the bus is actively driving

In any of these cases, the differential receiver will output a failsafe logic high state so that the output of the receiver is not indeterminate.

Receiver failsafe is accomplished by offsetting the receiver thresholds such that the *input indeterminate* range does not include zero volts differential. In order to comply with the RS-422 and RS-485 standards, the receiver output must output a high when the differential input V_{ID} is more positive than 200 mV, and must output a Low when V_{ID} is more negative than -200 mV. The receiver parameters which determine the failsafe performance are V_{TH+} , V_{TH-} , and V_{HYS} (the separation between V_{TH+} and V_{TH-}). As shown in the table, differential signals more negative than -200 mV will always cause a low receiver output, and differential signals more positive than 200 mV will always cause a high receiver output.

When the differential input signal is close to zero, it is still above the V_{TH+} threshold, and the receiver output will be High. Only when the differential input is more than V_{HYS} below V_{TH+} will the receiver output transition to a Low state. Therefore, the noise immunity of the receiver inputs during a bus fault conditions includes the receiver hysteresis value, V_{HYS} , as well as the value of V_{TH+} .



10.2.1.5 Transient Protection

The bus pins of the THVD14xx transceiver family include on-chip ESD protection against ± 30 -kV HBM and ± 18 -kV IEC 61000-4-2 contact discharge. The International Electrotechnical Commission (IEC) ESD test is far more severe than the HBM ESD test. The 50% higher charge capacitance, $C_{(S)}$, and 78% lower discharge resistance, $R_{(D)}$, of the IEC model produce significantly higher discharge currents than the HBM model. As stated in the IEC 61000-4-2 standard, contact discharge is the preferred transient protection test method.

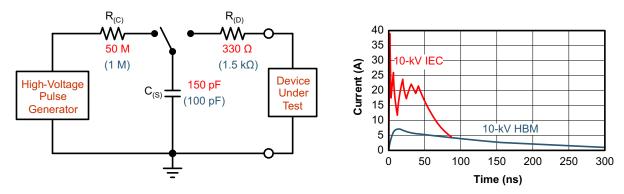


Figure 34. HBM and IEC ESD Models and Currents in Comparison (HBM Values in Parenthesis)

The on-chip implementation of IEC ESD protection significantly increases the robustness of equipment. Common discharge events occur because of human contact with connectors and cables. Designers may choose to implement protection against longer duration transients, typically referred to as surge transients.

EFTs are generally caused by relay-contact bounce or the interruption of inductive loads. Surge transients often result from lightning strikes (direct strike or an indirect strike which induce voltages and currents), or the switching of power systems, including load changes and short circuit switching. These transients are often encountered in industrial environments, such as factory automation and power-grid systems.

Figure 35 compares the pulse-power of the EFT and surge transients with the power caused by an IEC ESD transient. The left hand diagram shows the relative pulse-power for a 0.5-kV surge transient and 4-kV EFT transient, both of which dwarf the 10-kV ESD transient visible in the lower-left corner. 500-V surge transients are representative of events that may occur in factory environments in industrial and process automation.

The right hand diagram shows the pulse power of a 6-kV surge transient, relative to the same 0.5-kV surge transient. 6-kV surge transients are most likely to occur in power generation and power-grid systems.

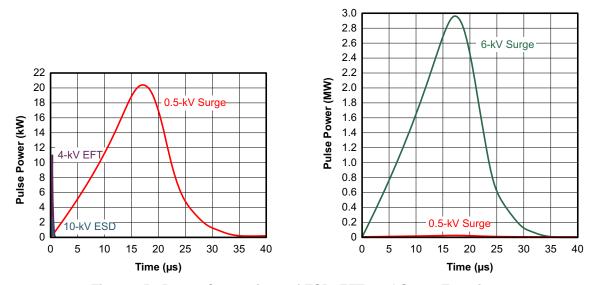


Figure 35. Power Comparison of ESD, EFT, and Surge Transients

If the surge transients, high-energy content is characterized by long pulse duration and slow decaying pulse power. The electrical energy of a transient that is dumped into the internal protection cells of a transceiver is converted into thermal energy, which heats and destroys the protection cells, thus destroying the transceiver. Figure 36 shows the large differences in transient energies for single ESD, EFT, surge transients, and an EFT pulse train that is commonly applied during compliance testing.

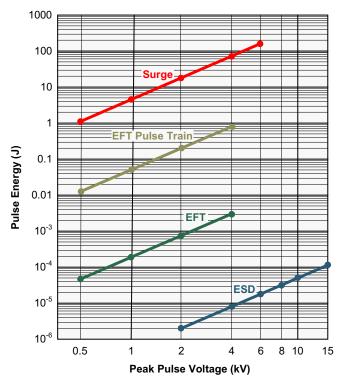


Figure 36. Comparison of Transient Energies



10.2.2 Detailed Design Procedure

Figure 37 and Figure 38 suggest a protection circuit against 1 kV surge (IEC 61000-4-5) transients. Table 7 shows the associated bill of materials.

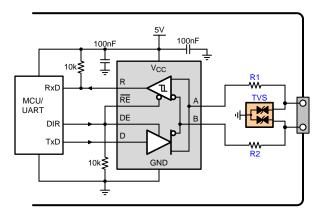


Figure 37. Transient Protection Against Surge Transients for Half-Duplex Devices

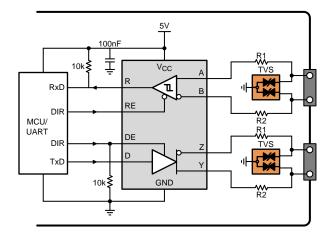
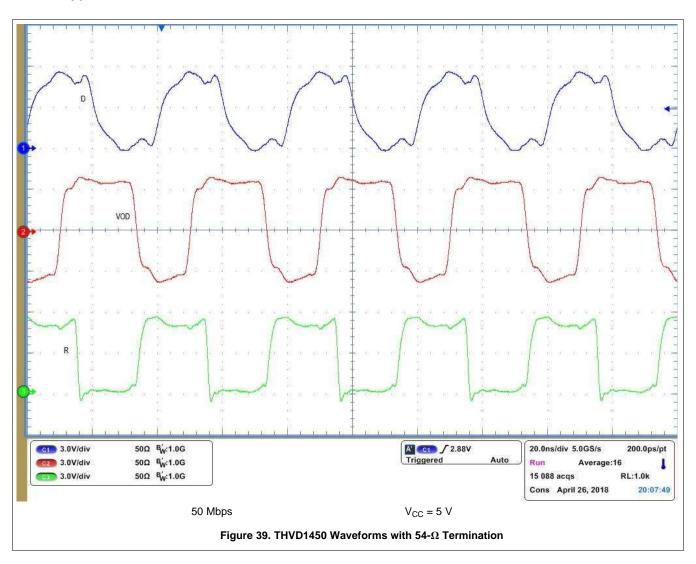


Figure 38. Transient Protection Against Surge Transients for Full-Duplex Devices

Table 7. Bill of Materials

DEVICE	FUNCTION	ORDER NUMBER	MANUFACTURER
XCVR	RS-485 transceiver	THVD14xx	TI
R1	40.0 mulas manefabiol. film manister	CDC/MOCOCOAOD INF ALID	Violence.
R2	10- Ω , pulse-proof thick-film resistor	CRCW0603010RJNEAHP	Vishay
TVS	Bidirectional 400-W transient suppressor	CDSOT23-SM712	Bourns

10.2.3 Application Curves



11 Power Supply Recommendations

To ensure reliable operation at all data rates and supply voltages, each supply should be decoupled with a 100 nF ceramic capacitor located as close to the supply pins as possible. This helps to reduce supply voltage ripple present on the outputs of switched-mode power supplies and also helps to compensate for the resistance and inductance of the PCB power planes.



12 Layout

12.1 Layout Guidelines

Robust and reliable bus node design often requires the use of external transient protection devices in order to protect against surge transients that may occur in industrial environments. Since these transients have a wide frequency bandwidth (from approximately 3 MHz to 300 MHz), high-frequency layout techniques should be applied during PCB design.

- Place the protection circuitry close to the bus connector to prevent noise transients from penetrating your board.
- 2. Use V_{CC} and ground planes to provide low-inductance. Note that high-frequency currents tend to follow the path of least impedance and not the path of least resistance.
- 3. Design the protection components into the direction of the signal path. Do not force the transient currents to divert from the signal path to reach the protection device.
- 4. Apply 100-nF to 220-nF decoupling capacitors as close as possible to the V_{CC} pins of transceiver, UART and/or controller ICs on the board.
- 5. Use at least two vias for V_{CC} and ground connections of decoupling capacitors and protection devices to minimize effective via inductance.
- 6. Use 1-k Ω to 10-k Ω pull-up and pull-down resistors for enable lines to limit noise currents in theses lines during transient events.
- 7. Insert pulse-proof resistors into the A and B bus lines if the TVS clamping voltage is higher than the specified maximum voltage of the transceiver bus pins. These resistors limit the residual clamping current into the transceiver and prevent it from latching up.
- 8. While pure TVS protection is sufficient for surge transients up to 1 kV, higher transients require metal-oxide varistors (MOVs) which reduce the transients to a few hundred volts of clamping voltage, and transient blocking units (TBUs) that limit transient current to less than 1 mA.

12.2 Layout Example

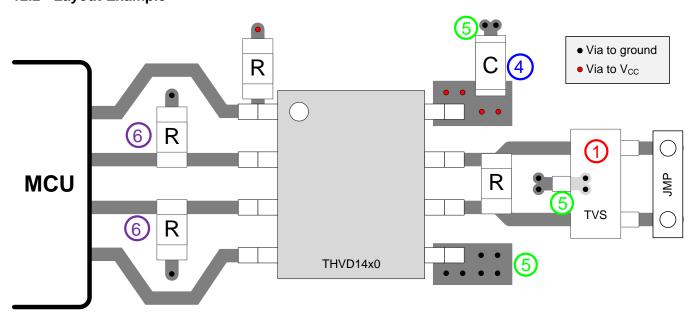


Figure 40. Half-Duplex Layout Example

13 Device and Documentation Support

13.1 Device Support

13.2 Third-Party Products Disclaimer

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13.3 Related Links

The table below lists quick access links. Categories include technical documents, support and community resources, tools and software, and quick access to order now.

TECHNICAL TOOLS & SUPPORT & PRODUCT FOLDER **PARTS ORDER NOW DOCUMENTS SOFTWARE** COMMUNITY **THVD1410** Click here Click here Click here Click here Click here THVD1450 Click here Click here Click here Click here Click here THVD1451 Click here Click here Click here Click here Click here THVD1452 Click here Click here Click here Click here Click here

Table 8. Related Links

13.4 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on ti.com. In the upper right corner, click on *Alert me* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document..

13.5 Community Resources

The following links connect to TI community resources. Linked contents are provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's Terms of Use.

TI E2E™ Online Community *TI's Engineer-to-Engineer (E2E) Community.* Created to foster collaboration among engineers. At e2e.ti.com, you can ask questions, share knowledge, explore ideas and help solve problems with fellow engineers.

Design Support *TI's Design Support* Quickly find helpful E2E forums along with design support tools and contact information for technical support.

13.6 Trademarks

E2E is a trademark of Texas Instruments.

All other trademarks are the property of their respective owners.

13.7 Electrostatic Discharge Caution



These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

13.8 Glossary

SLYZ022 — TI Glossary.

This glossary lists and explains terms, acronyms, and definitions.



14 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

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3-Dec-2024

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material (6)	MSL Peak Temp	Op Temp (°C)	Device Marking (4/5)	Samples
THVD1410D	ACTIVE	SOIC	D	8	75	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	VD1410	Samples
THVD1410DGK	ACTIVE	VSSOP	DGK	8	80	RoHS & Green	NIPDAUAG	Level-1-260C-UNLIM	-40 to 125	1410	Samples
THVD1410DGKR	ACTIVE	VSSOP	DGK	8	2500	RoHS & Green	NIPDAU SN NIPDAUAG	Level-1-260C-UNLIM	-40 to 125	1410	Samples
THVD1410DR	ACTIVE	SOIC	D	8	2500	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	VD1410	Samples
THVD1450D	ACTIVE	SOIC	D	8	75	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	VD1450	Samples
THVD1450DGK	ACTIVE	VSSOP	DGK	8	80	RoHS & Green	NIPDAUAG	Level-1-260C-UNLIM	-40 to 125	1450	Samples
THVD1450DGKR	ACTIVE	VSSOP	DGK	8	2500	RoHS & Green	NIPDAUAG SN	Level-1-260C-UNLIM	-40 to 125	1450	Samples
THVD1450DR	ACTIVE	SOIC	D	8	2500	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	VD1450	Samples
THVD1450DRBR	ACTIVE	SON	DRB	8	3000	RoHS & Green	SN	Level-1-260C-UNLIM	-40 to 125	1450	Samples
THVD1450DRBT	ACTIVE	SON	DRB	8	250	RoHS & Green	SN	Level-1-260C-UNLIM	-40 to 125	1450	Samples
THVD1451D	ACTIVE	SOIC	D	8	75	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	VD1451	Samples
THVD1451DR	ACTIVE	SOIC	D	8	2500	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	VD1451	Samples
THVD1451DRBR	ACTIVE	SON	DRB	8	3000	RoHS & Green	SN	Level-1-260C-UNLIM	-40 to 125	1451	Samples
THVD1451DRBT	ACTIVE	SON	DRB	8	250	RoHS & Green	SN	Level-1-260C-UNLIM	-40 to 125	1451	Samples
THVD1452D	ACTIVE	SOIC	D	14	50	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	1452	Samples
THVD1452DGS	ACTIVE	VSSOP	DGS	10	80	RoHS & Green	NIPDAUAG	Level-1-260C-UNLIM	-40 to 125	1452	Samples
THVD1452DGSR	ACTIVE	VSSOP	DGS	10	2500	RoHS & Green	NIPDAUAG	Level-1-260C-UNLIM	-40 to 125	1452	Samples
THVD1452DR	ACTIVE	SOIC	D	14	2500	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	1452	Samples

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.



PACKAGE OPTION ADDENDUM

www.ti.com 3-Dec-2024

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (CI) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

- (3) MSL, Peak Temp. The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.
- (4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.
- (5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.
- (6) Lead finish/Ball material Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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www.ti.com 5-Nov-2024

TAPE AND REEL INFORMATION





A0	Dimension designed to accommodate the component width
В0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
THVD1410DGKR	VSSOP	DGK	8	2500	330.0	12.4	5.3	3.4	1.4	8.0	12.0	Q1
THVD1410DGKR	VSSOP	DGK	8	2500	330.0	12.4	5.25	3.35	1.25	8.0	12.0	Q1
THVD1410DR	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
THVD1450DGKR	VSSOP	DGK	8	2500	330.0	12.4	5.3	3.4	1.4	8.0	12.0	Q1
THVD1450DR	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
THVD1450DRBR	SON	DRB	8	3000	330.0	12.4	3.3	3.3	1.0	8.0	12.0	Q2
THVD1450DRBT	SON	DRB	8	250	180.0	12.4	3.3	3.3	1.0	8.0	12.0	Q2
THVD1451DR	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
THVD1451DRBR	SON	DRB	8	3000	330.0	12.4	3.3	3.3	1.0	8.0	12.0	Q2
THVD1451DRBT	SON	DRB	8	250	180.0	12.4	3.3	3.3	1.0	8.0	12.0	Q2
THVD1452DGSR	VSSOP	DGS	10	2500	330.0	12.4	5.3	3.4	1.4	8.0	12.0	Q1
THVD1452DR	SOIC	D	14	2500	330.0	16.4	6.5	9.0	2.1	8.0	16.0	Q1



www.ti.com 5-Nov-2024



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	Pins SPQ Length (Width (mm)	Height (mm)
THVD1410DGKR	VSSOP	DGK	8	2500	353.0	353.0	32.0
THVD1410DGKR	VSSOP	DGK	8	2500	366.0	364.0	50.0
THVD1410DR	SOIC	D	8	2500	353.0	353.0	32.0
THVD1450DGKR	VSSOP	DGK	8	2500	364.0	364.0	27.0
THVD1450DR	SOIC	D	8	2500	353.0	353.0	32.0
THVD1450DRBR	SON	DRB	8	3000	346.0	346.0	35.0
THVD1450DRBT	SON	DRB	8	250	200.0	183.0	25.0
THVD1451DR	SOIC	D	8	2500	353.0	353.0	32.0
THVD1451DRBR	SON	DRB	8	3000	346.0	346.0	35.0
THVD1451DRBT	SON	DRB	8	250	200.0	183.0	25.0
THVD1452DGSR	VSSOP	DGS	10	2500	364.0	364.0	27.0
THVD1452DR	SOIC	D	14	2500	353.0	353.0	32.0

PACKAGE MATERIALS INFORMATION

www.ti.com 5-Nov-2024

TUBE



*All dimensions are nominal

Device	Package Name	Package Type	Pins	SPQ	L (mm)	W (mm)	T (µm)	B (mm)
THVD1410D	D	SOIC	8	75	507	8	3940	4.32
THVD1410DGK	DGK	VSSOP	8	80	330	6.55	500	2.88
THVD1450D	D	SOIC	8	75	507	8	3940	4.32
THVD1450DGK	DGK	VSSOP	8	80	330	6.55	500	2.88
THVD1451D	D	SOIC	8	75	507	8	3940	4.32
THVD1452D	D	SOIC	14	50	507	8	3940	4.32
THVD1452DGS	DGS	VSSOP	10	80	330	6.55	500	2.88





PowerPAD is a trademark of Texas Instruments.

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

 2. This drawing is subject to change without notice.

 3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not
- exceed 0.15 mm per side.
- 4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm per side.
- 5. Reference JEDEC registration MO-187.





- 6. Publication IPC-7351 may have alternate designs.
- 7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.
- 8. Vias are optional depending on application, refer to device data sheet. If any vias are implemented, refer to their locations shown on this view. It is recommended that vias under paste be filled, plugged or tented.
- 9. Size of metal pad may vary due to creepage requirement.





- 11. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 12. Board assembly site may have different recommendations for stencil design.





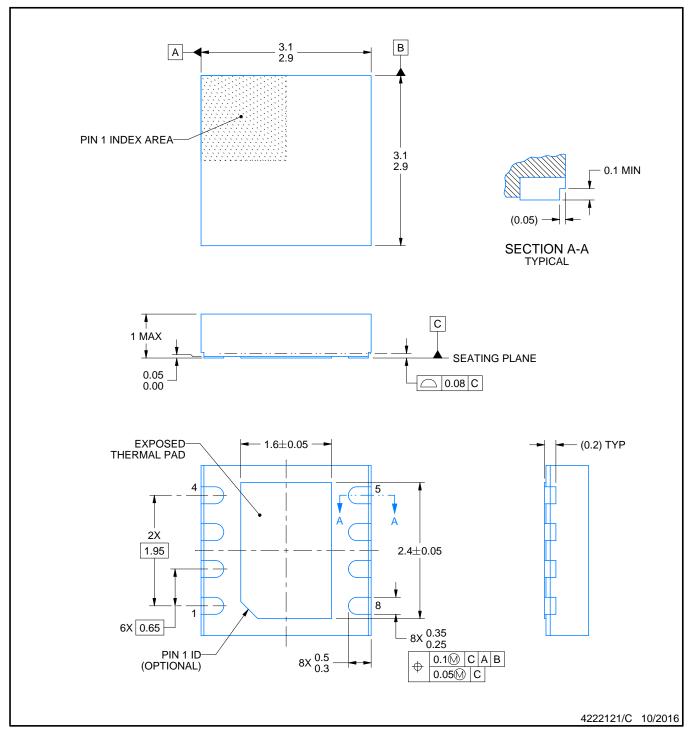
Images above are just a representation of the package family, actual package may vary. Refer to the product data sheet for package details.

4203482/L





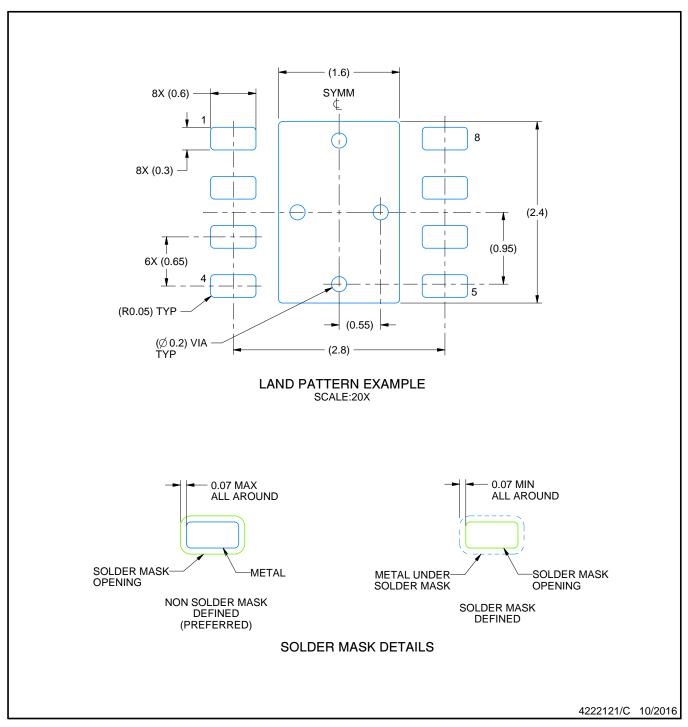
PLASTIC SMALL OUTLINE - NO LEAD



- All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
- 2. This drawing is subject to change without notice.
- 3. The package thermal pad must be soldered to the printed circuit board for thermal and mechanical performance.



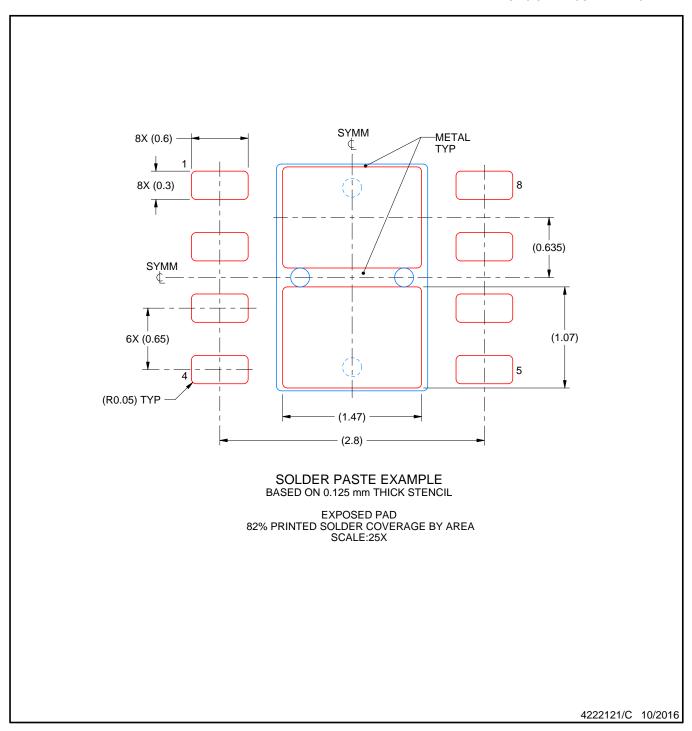
PLASTIC SMALL OUTLINE - NO LEAD



- 4. This package is designed to be soldered to a thermal pad on the board. For more information, see Texas Instruments literature number SLUA271 (www.ti.com/lit/slua271).
- Vias are optional depending on application, refer to device data sheet. If any vias are implemented, refer to their locations shown on this view. It is recommended that vias under paste be filled, plugged or tented.



PLASTIC SMALL OUTLINE - NO LEAD



NOTES: (continued)

6. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.







- 1. All linear dimensions are in millimeters. Dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

 2. This drawing is subject to change without notice.

 3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not
- exceed 0.15 mm, per side.
- 4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.43 mm, per side.
- 5. Reference JEDEC registration MS-012, variation AB.





NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.





- 8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 9. Board assembly site may have different recommendations for stencil design.







- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

 2. This drawing is subject to change without notice.

 3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not
- exceed 0.15 mm per side.
- 4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm per side.
- 5. Reference JEDEC registration MO-187, variation BA.





NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.





- 8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 9. Board assembly site may have different recommendations for stencil design.







- 1. Linear dimensions are in inches [millimeters]. Dimensions in parenthesis are for reference only. Controlling dimensions are in inches. Dimensioning and tolerancing per ASME Y14.5M.
- 2. This drawing is subject to change without notice.
- 3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed .006 [0.15] per side.
- 4. This dimension does not include interlead flash.
- 5. Reference JEDEC registration MS-012, variation AA.





NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.





- 8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 9. Board assembly site may have different recommendations for stencil design.



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